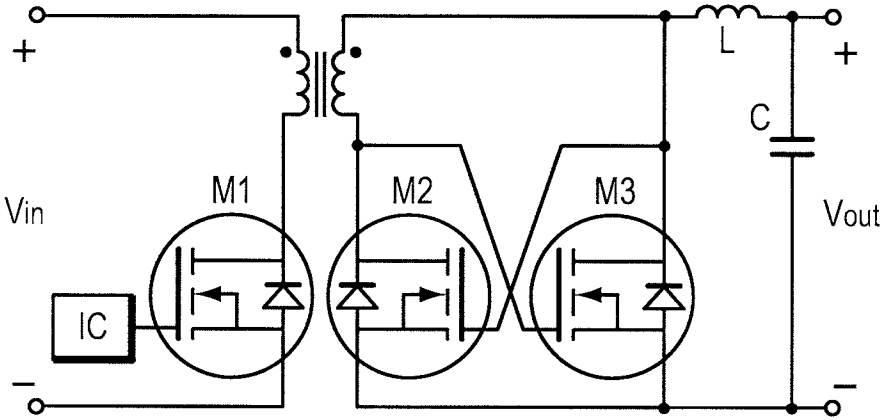
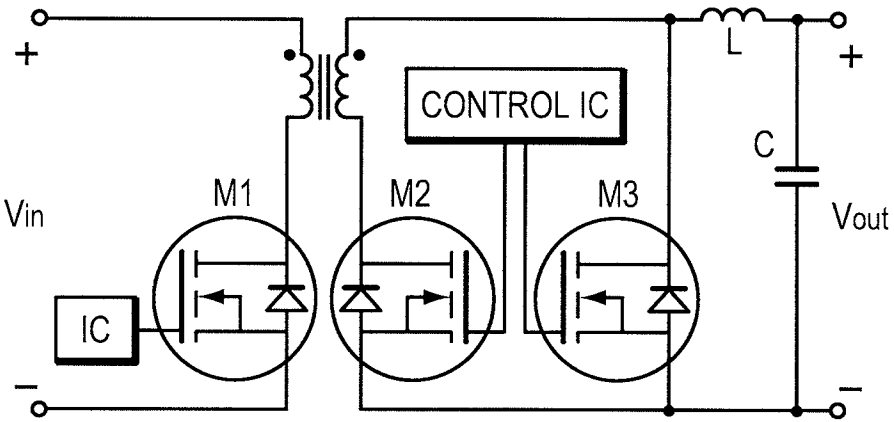


SELF-DRIVEN SYNCHRONOUS RECTIFICATION
ISOLATED FORWARD CONVERTER

FIG. 1A



IC-DRIVEN SYNCHRONOUS RECTIFICATION
ISOLATED FORWARD CONVERTER

FIG. 1B

Title: "Monolithic Power Semiconductor Structures Including Pairs of Integrated Devices"
Inventors: Shen *et al.*
Serial No. 10/582,035
Atty Docket No. GWS-009
Attorney: Natasha C. Us
REPLACEMENT SHEET 1 of 11

Title: "Monolithic Power Semiconductor Structures Including Pairs of Integrated Devices"
Inventors: Shen *et al.*
Serial No. 10/582,035
Atty Docket No. GWS-009
Attorney: Natasha C. Us
REPLACEMENT SHEET 2 of 11

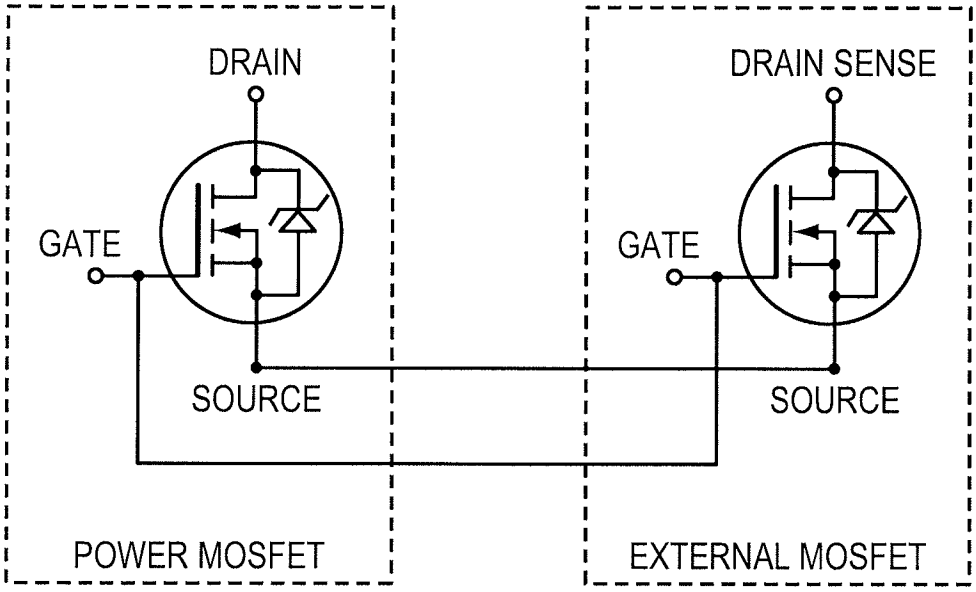


FIG. 2

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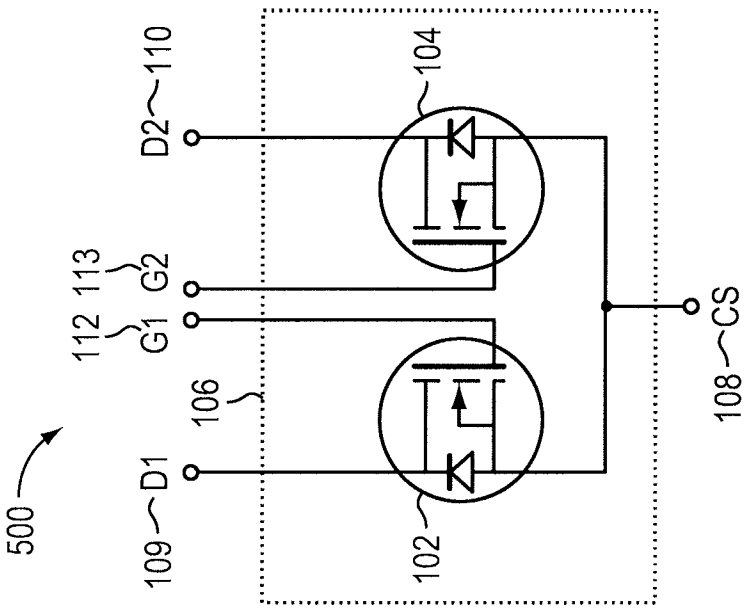
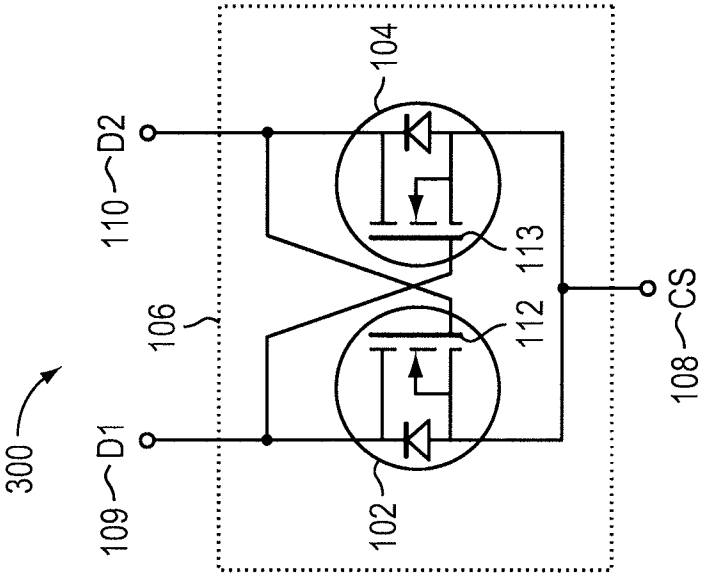
Inventors: Shen *et al.*
Serial No. 10/582,035
Atty Docket No. GWS-009
Attorney: Natasha C. Us
REPLACEMENT SHEET 3 of 11



SECOND EMBODIMENT:
5-LEAD CONTROL IC-DRIVEN
SYNCHRONOUS RECTIFICATION
MOSFET PAIR

FIG. 3B



FIRST EMBODIMENT:
3-LEAD SELF-DRIVEN
SYNCHRONOUS RECTIFICATION
MOSFET PAIR

FIG. 3A

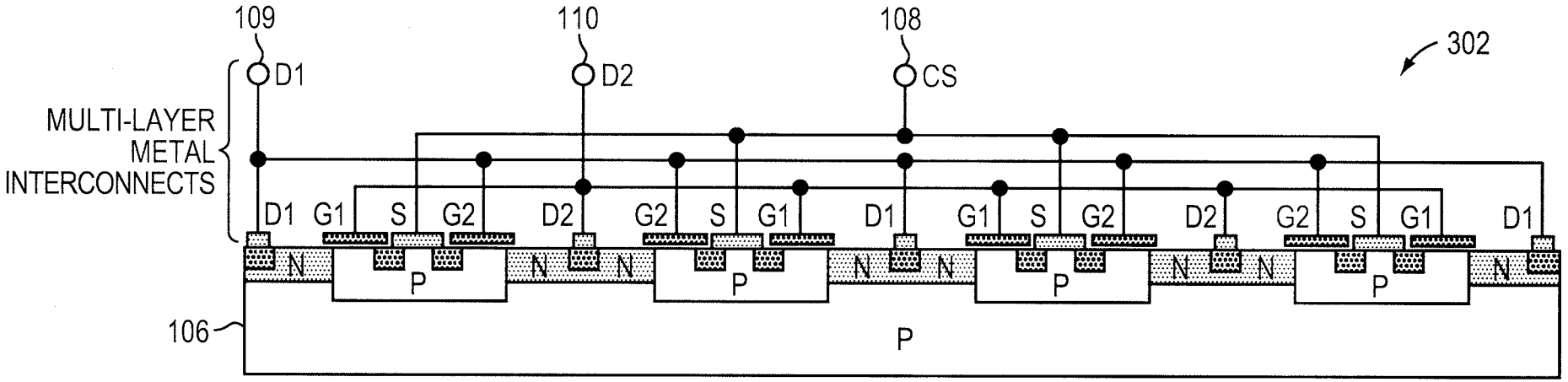


FIG. 4A

FIRST EMBODIMENT: 3-LEAD SELF-DRIVEN MOSFET PAIR IN INTERLEAVED CELL FINGERS

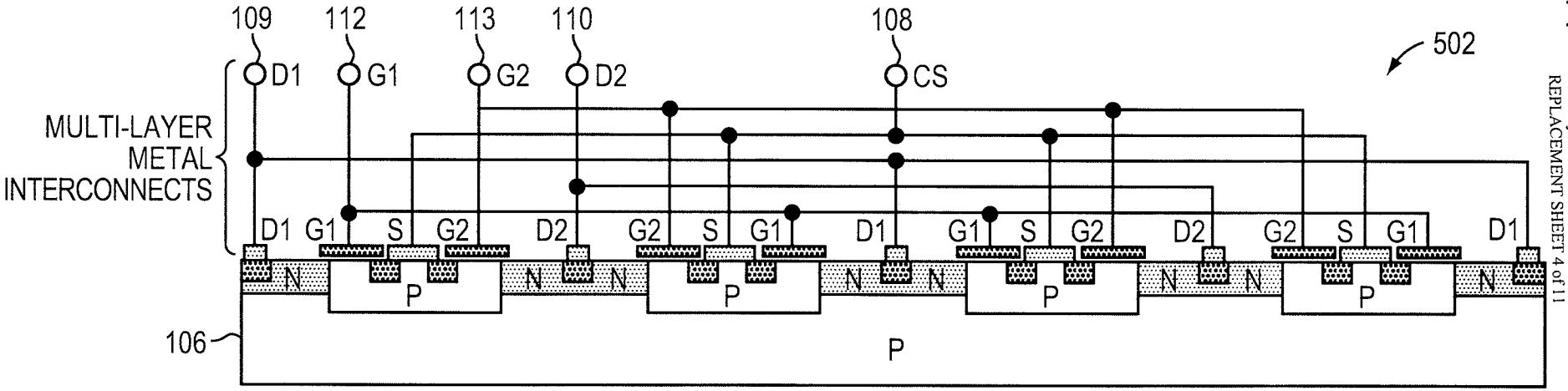


FIG. 4B

SECOND EMBODIMENT: 5-LEAD EXTERNAL-DRIVEN MOSFET PAIR IN INTERLEAVED CELL FINGERS

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REPLACEMENT SHEET 4 of 11

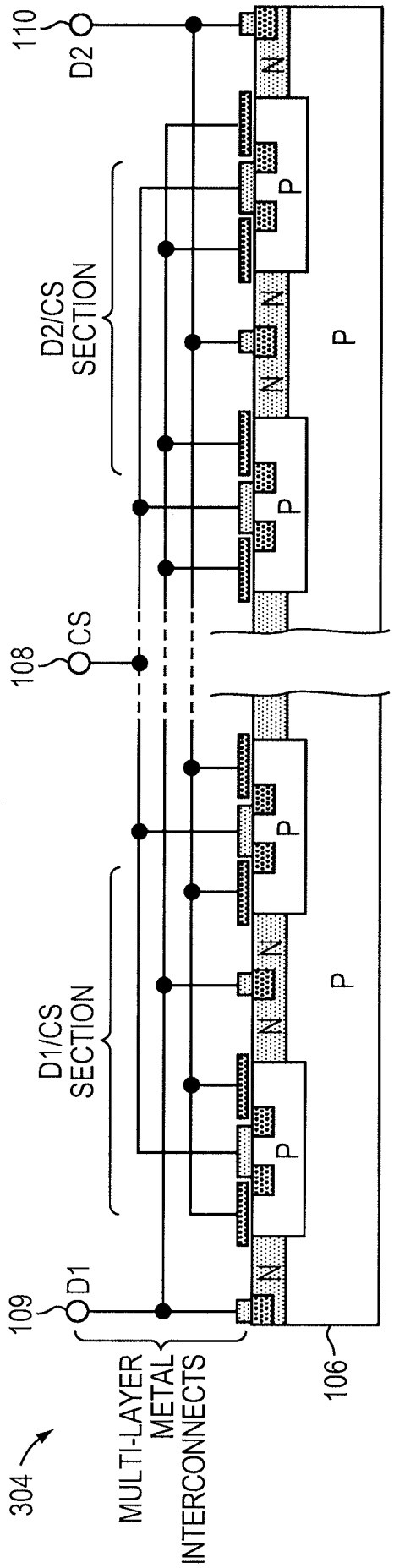

FIG. 5A

THIRD EMBODIMENT: 3-LEAD SELF-DRIVEN MOSFET PAIR IN SEPARATE CELL SECTIONS

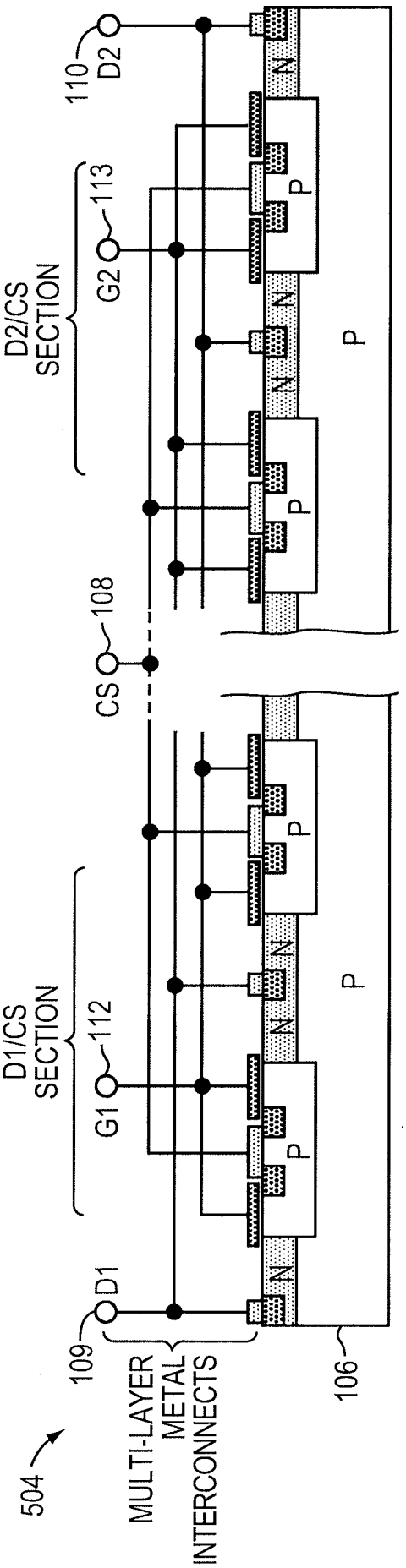

FIG. 5B

FOURTH EMBODIMENT: 5-LEAD EXTERNAL-DRIVEN MOSFET PAIR IN SEPARATE CELL SECTIONS

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REPLACEMENT SHEET 6 of 11

1. DISCRETE POWER SEMICONDUCTOR DEVICE COMPRISED OF MULTIPLE TRANSISTORS WITH COMMON SOURCE CONNECTION WITH ONE OR MORE TRANSISTORS HAVING ELECTRICALLY ISOLATED DRAIN AND GATE CONNECTIONS

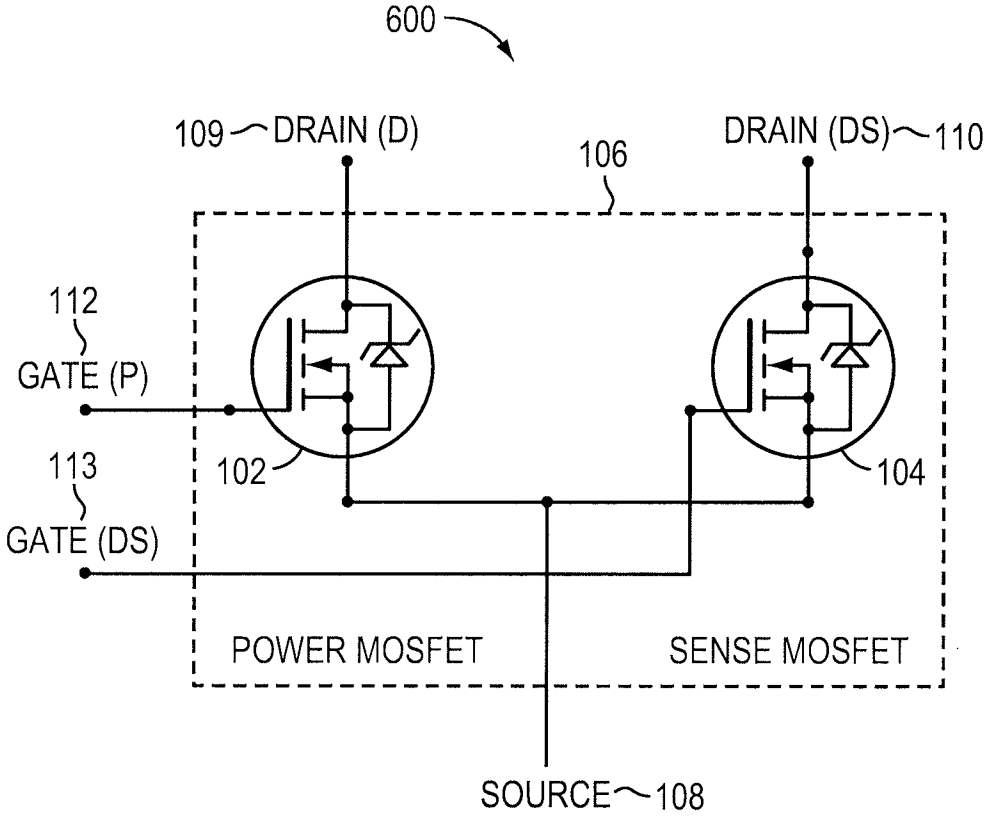

FIG. 6

1. DISCRETE POWER SEMICONDUCTOR DEVICE COMPRISED OF MULTIPLE TRANSISTORS WITH COMMON SOURCE CONNECTION WITH ONE OR MORE TRANSISTORS HAVING ELECTRICALLY ISOLATED DRAIN AND GATE CONNECTIONS

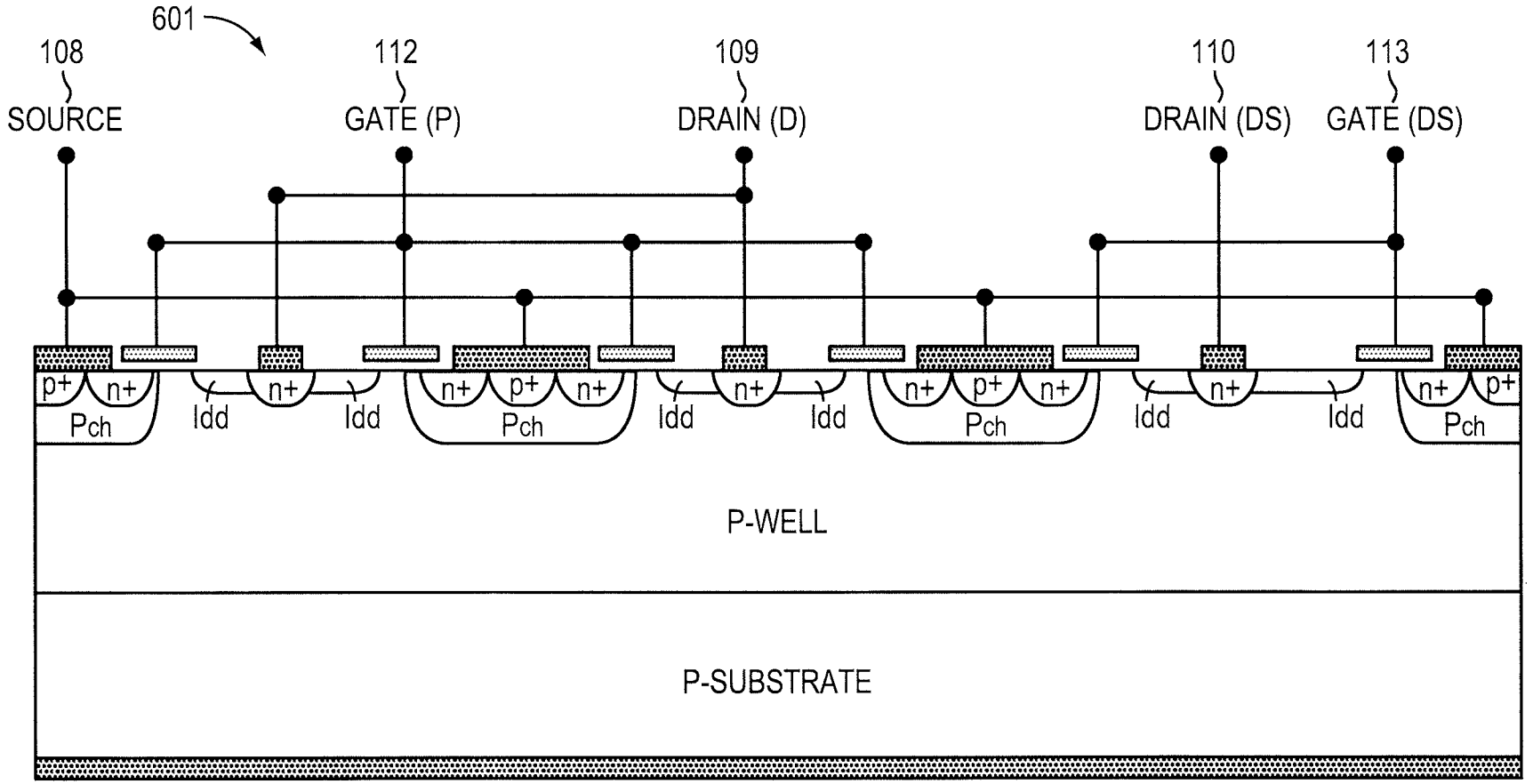

FIG. 7

CROSS-SECTIONAL DIAGRAM OF A POWER MOSFET WITH INTEGRATED DRAIN SENSE

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Title: "Monolithic Power Semiconductor Structures Including Pairs of Integrated Devices"
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Serial No. 10/582,035
Atty Docket No. GWS-009
Attorney: Natasha C. Us
REPLACEMENT SHEET 8 of 11

2. DISCRETE POWER SEMICONDUCTOR DEVICE COMPRISED OF MULTIPLE TRANSISTORS WITH COMMON SOURCE AND GATE CONNECTIONS WITH ONE OR MORE TRANSISTORS HAVING ELECTRICALLY ISOLATED DRAIN CONNECTIONS

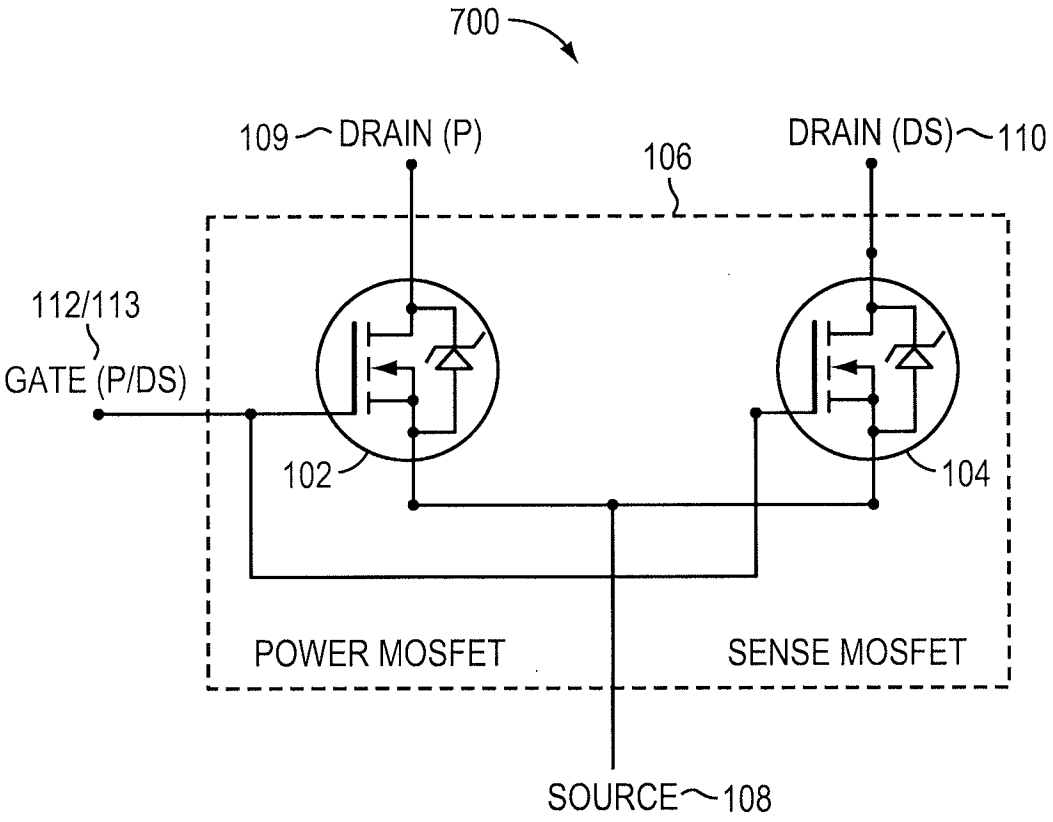

FIG. 8

2. DISCRETE POWER SEMICONDUCTOR DEVICE COMPRISED OF MULTIPLE TRANSISTORS WITH COMMON SOURCE AND GATE CONNECTIONS WITH ONE OR MORE TRANSISTORS HAVING ELECTRICALLY ISOLATED DRAIN CONNECTIONS

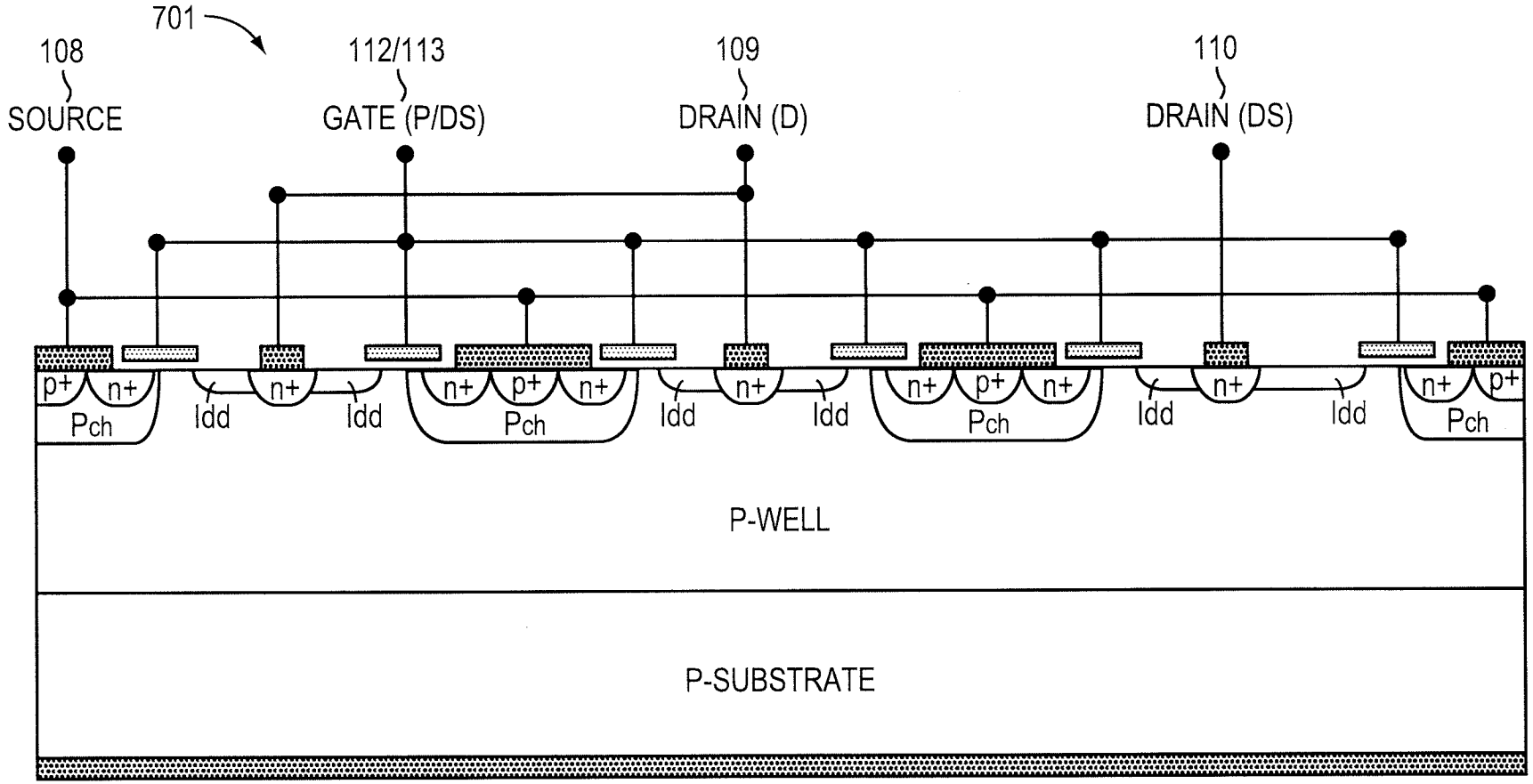

FIG. 9

CROSS-SECTIONAL DIAGRAM OF A POWER MOSFET WITH INTEGRATED DRAIN SENSE

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Inventors: Shen *et al.*
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Atty Docket No. GWS-009
Attorney: Natasha C. Us
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Title: "Monolithic Power Semiconductor Structures Including Pairs of Integrated Devices"
Inventors: Shen *et al.*
Serial No. 10/582,035
Atty Docket No. GWS-009
Attorney: Natasha C. Us
REPLACEMENT SHEET 10 of 11

3. DISCRETE POWER SEMICONDUCTOR DEVICE COMPRISED OF MULTIPLE TRANSISTORS WITH COMMON SOURCE AND GATE CONNECTIONS WITH ONE OR MORE TRANSISTORS HAVING SUBSTANTIALLY DIFFERENT THRESHOLD VOLTAGES AND ELECTRICALLY ISOLATED DRAIN CONNECTIONS

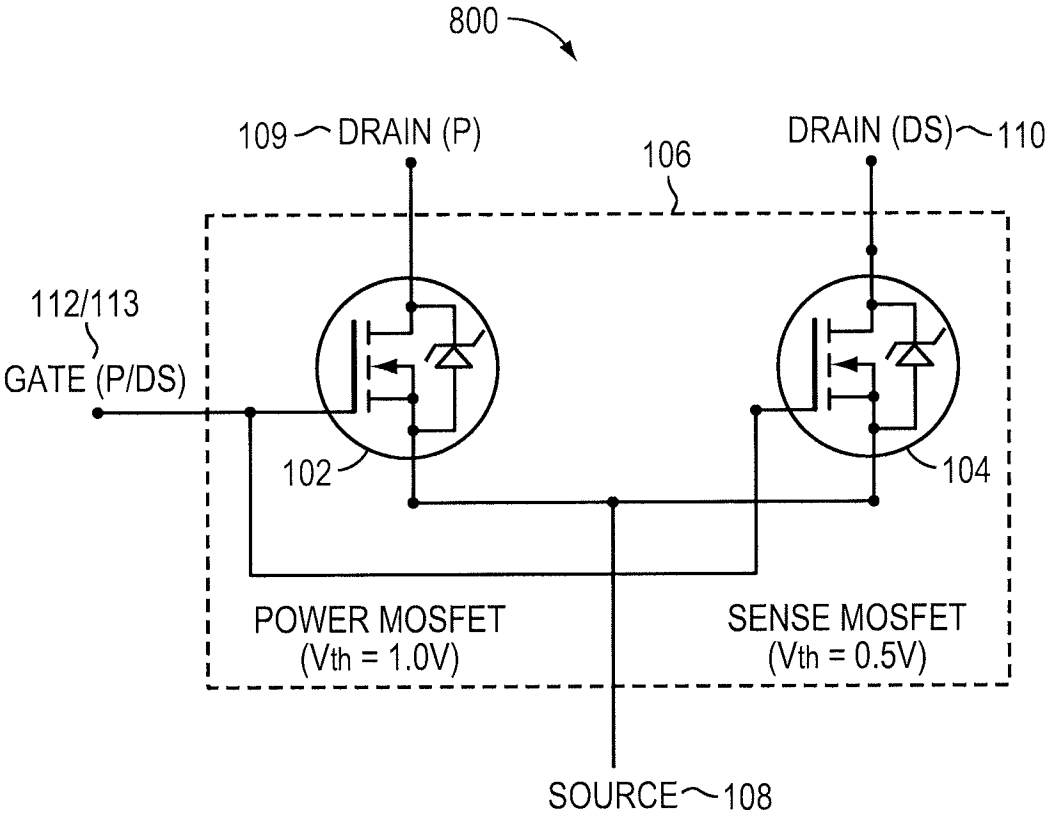

FIG. 10

3. DISCRETE POWER SEMICONDUCTOR DEVICE COMPRISED OF MULTIPLE TRANSISTORS WITH COMMON SOURCE AND GATE CONNECTIONS WITH ONE OR MORE TRANSISTORS HAVING SUBSTANTIALLY DIFFERENT THRESHOLD VOLTAGES AND ELECTRICALLY ISOLATED DRAIN CONNECTIONS

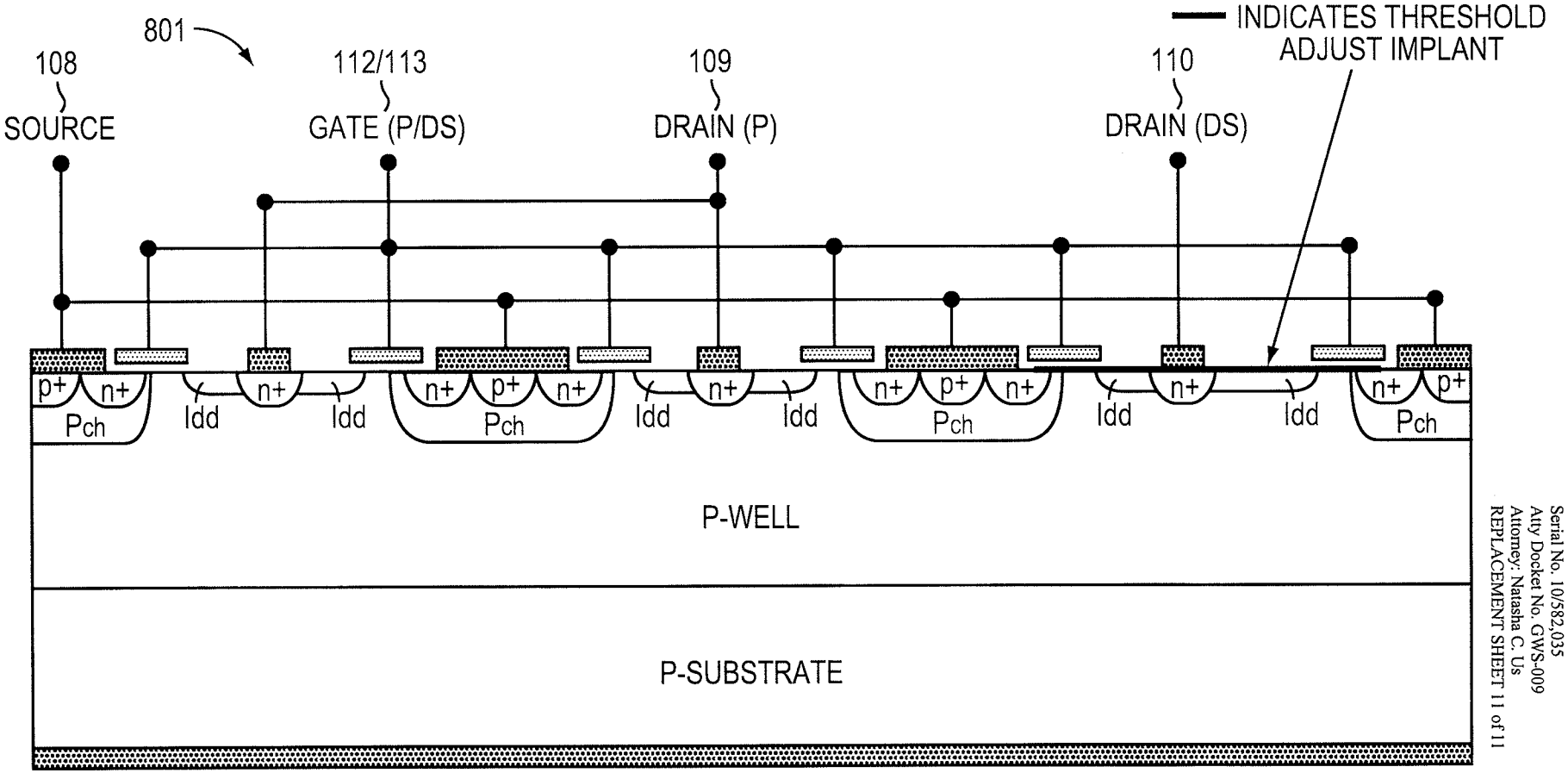

FIG. 11

CROSS-SECTIONAL DIAGRAM OF A POWER MOSFET WITH INTEGRATED DRAIN SENSE

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Inventors: Shen *et al.*
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Atty Docket No. GWS-009
Attorney: Natasha C. Us
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